

Spin blockade in a charge-switchable molecular magnet

C. Romeike,* M. R. Wegewijs, and H. Schoeller
*Institut für Theoretische Physik A, RWTH Aachen,
 52056 Aachen, Germany*
 (Dated: February 2, 2008)

We consider the effect of adding electrons to a single molecule on its magnetic properties and the resulting transport fingerprints. We analyze a generic model for a metal-organic complex consisting of orbitals with different Coulomb repulsions. We find that by modulating the charge of the molecule by a single electron the total spin can be switched from zero to the maximal value supported by the added electrons, $S = 3/2$. The Nagaoka mechanism is responsible for this charge-sensitivity of the molecular spin. It is shown that fingerprints of these maximal spin states, either as groundstates or low-lying excitations, can be experimentally observed in current-spectroscopy as either spin blockade at low bias voltage or negative differential conductance and complete current suppression at finite bias.

PACS numbers:

Introduction — Recent experiments on metal-organic *grid complexes*, consisting of rationally designed ligands and metal ions as building units have exhibited interesting electrochemical [1, 2] and magnetic [3, 4, 5] properties. By self-assembly the metal ions and ligands arrange in a rigid, highly symmetric grid. Due to their different nature, electron orbitals can often be roughly attributed either to the metal-ions or the ligands. Typically the orbitals on the (organic) ligands have π symmetry whereas the d metal orbitals split in an e.g. octahedral ligand field into subshells with local π and σ symmetry. In the case of a fully occupied d_π subshell tunneling between ligand π orbitals and metal d_σ orbitals is weak due to their different symmetry. Such a separation into metal ion and ligand units has been used successfully to describe the low-temperature intramolecular spin coupling of Co-[2×2] grids [6, 7] and Mn-[3×3] grids [4, 5] for a fixed charge state as well as the electrochemical properties of (Mn, Fe, Co, Zn)-[2×2] [8] and Mn-[3×3] grids [2]. For poly-pyridine complexes it is well-known [9] that ligands as well as metal ions can be reduced. Which type is preferred depends on chemical details which can be controlled, mainly by substitution of metal ions and changing the ligand. Here we analyze a phenomenological low temperature model for a [2×2] grid molecule consisting of four ions and four ligands, Fig. 1. For this particular structure we show that (i) the molecular spin can be switched by the charge and (ii) the spin-splitting appears in tunneling spectroscopy. The well known Nagaoka mechanism [10] becomes effective for certain numbers of added electrons. For strong onsite interaction the delocalization of an extra hole/electron relative to half-filling (favoring a fully polarized background of all other electrons) dominates over an antiferromagnetic superexchange. In the context of band-magnetism the

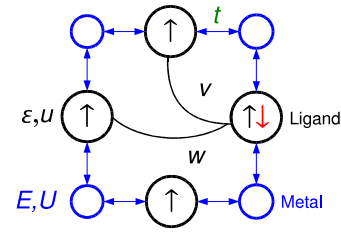


FIG. 1: Grid molecule: small/large circles represent metal ion/ligand orbitals.

relevance of this mechanism is limited due to its lattice type dependence [11] and its strong charge sensitivity. Only for a single additional electron or hole relative to a half-filled band, the spin-polarization effect can be guaranteed. In small single-molecule devices these obstacles can be overcome. Firstly, the advanced rational design of supramolecular structures allows complex “lattice” types to be realized [1, 12]. Secondly, due to the Coulomb blockade effect one can modulate the total charge of a molecule by a *single* electron [13, 14, 15]. In the case of sufficiently strong short-range interaction on the ligands (relative to the ligand-ion tunneling) the ground state spin is maximally increased from $S = 0$ to the maximal value supported by 3 (or 5) extra electrons on the molecule, $S = 3/2$. The magnetic properties of the molecule can thus be controlled electrically [16, 17]. In single electron tunneling transport this leads to spin blockade at low bias voltage. Even for a low-lying maximal spin excitation negative differential conductance (NDC) effects and complete current suppression at finite bias voltage occur. Similar models with two types of electron orbitals have been studied for the description of the neutral-ionic transition [18] in organic crystals, in the context of ferroelectrics and superconductivity in transition-metal oxides [19] and recently in the context of exotic Kondo effects due to dynamical symmetries in multi quantum-dot systems [20, 21].

*Electronic address: romeike@physik.rwth-aachen.de

Model— We consider a model of a grid-complex with

four metal and four ligand sites and one orbital per site (Fig. 1). For simplicity, we assume that the metal ion can only be occupied virtually. The strong ligand field separates electron accepting d orbitals energetically from ligand orbitals. Additionally, Coulomb repulsion on the ions is typically much stronger than on the ligands. The following Hamiltonian captures the features of the electronic degrees of freedom:

$$H_{\text{mol}} = H_{\text{T}} + H_{\text{L}} + H_{\text{M}}, \quad (1)$$

$$H_{\text{T}} = \sum_{\langle i,j \rangle} \sum_{\sigma} t A_{i\sigma}^{\dagger} a_{j\sigma} + h.c. \quad (2)$$

$$H_{\text{L}} = \sum_{j=1}^4 (\epsilon n_j + u n_{j\uparrow} n_{j\downarrow} + v n_j n_{j+1}) + w \sum_{j=1}^2 n_j n_{j+2} \quad (3)$$

$$H_{\text{M}} = \sum_{i=1}^4 (E N_i + U N_{i\uparrow} N_{i\downarrow}) \quad (4)$$

Operators and variables (except t) in lower/upper case relate to the ligands/metal ion and all indices run from 1 to 4 cyclically. $\langle i, j \rangle$ denotes a summation over neighboring metal ions i and ligands j . The operator $a_{j\sigma}^{\dagger}$ creates an electron on ligand site j with spin σ , $n_{j\sigma} = a_{j\sigma}^{\dagger} a_{j\sigma}$ and $n_j = \sum_{\sigma} n_{j\sigma}$. Similar definitions hold for the metal ions: $A_{i\sigma}, N_{i\sigma} = A_{i\sigma}^{\dagger} A_{i\sigma}, N_i = \sum_{\sigma} N_{i\sigma}$. The tunneling term (2) describes hopping between ligand and metal ions and is assumed to be independent of i and j due to molecular symmetry. The ligand-part of the Hamiltonian (3) consists of an orbital with energy ϵ , the Coulomb repulsion terms on the ligand (u) and between adjacent (v) and opposite ligands (w). Due to decreasing overlap with distance we have $u > v > w$. Hamiltonian (4) describes the isolated metal ion orbitals with energy E . Here we only consider the short-range interaction U because the d orbital overlap between two ions is typically much smaller than that between two ligand orbitals. In Fig. 1 these interactions are schematically indicated. We study the parameter regime where the first eight extra *electrons occupy* four equivalent *ligand centered orbitals*. Such a sequence has been well-documented for a number of grid-molecules [8]. In our model this is the case when the charge excitations of the ligand lie below the ones of the metal ion: $\epsilon < \epsilon + u < E < E + U$. The metal ligand charge-transfer barrier $\Delta = \epsilon - E$ suppresses the direct hopping of extra electrons from the ligands to unoccupied metal ions: $|\Delta| \gg t$. The fluctuations of the metal orbital occupation around zero can be treated using a Schrieffer-Wolff transformation [22]. We obtain an extended Hubbard model $H_{\text{eff}} = \sum_{\langle jk \rangle} \sum_{\sigma} t_{\text{eff}} a_{j\sigma}^{\dagger} a_{k\sigma} + H_{\text{L}}$ on four ligand sites with an effective hopping matrix element $t_{\text{eff}} = -\frac{t^2}{2\Delta}$.

Addition energies and spin states — We first analyze the

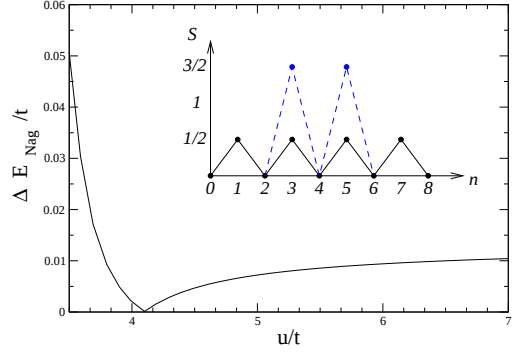


FIG. 2: Splitting ΔE_{Nag} for $n = 3$ as function of u for $v = 2.25t, w = 1t, \Delta = -10t, t_{\text{eff}} = 0.05t$. For $u_{\text{th}} \approx 4.15t = 83t_{\text{eff}}$ the ground state has maximal spin. Inset: ground state spin as function of the number of electrons n added to the ligands for $u < u_{\text{th}}$ (solid black line) and $u > u_{\text{th}}$ (dashed blue line).

electronic spectrum of H_{eff} for different charge sectors. In the case $u > v > w/2 > t_{\text{eff}}$ the first electron reduces one of the four ligands, say $j = 1$. The next one occupies the opposite ligand $j = 3$ in order to minimize the Coulomb interaction. The next electrons reduce the adjacent ligands $j = 2, 4$. This sequence is repeated for the next four electrons, each time doubly occupying a ligand orbital. The gaps in the addition spectrum $w, 2v - w, w, u, w, 2v - w, w$ (extra energy required for the next electron) thus directly relate to geometrical features of the grid [8]. These electrostatic parameters correspond directly to the size of the Coulomb diamonds obtained in transport experiments. Now we discuss the ground state spin as successive electrons are added to the molecule. Due to superexchange processes electron spins on neighboring ligands tend to couple antiferromagnetically. This leads to an alternating sequence of $S = 0$ and $S = 1/2$ as electrons are added (inset Fig. 2). However, for *sufficiently large* $u > u_{\text{th}}$ and fixed t , resp. t_{eff} (Fig. 2) the ground state spin for $n = 3, 5$ is enhanced from the noninteracting value $S = 1/2$ to the maximal possible value $S = 3/2$. Because double occupation is suppressed, a single hole/electron (relative to the half-filled state $n = 4$) can maximally gain kinetic energy when the background of the other electrons is fully spin polarized. This is the underlying mechanism for the Nagaoka theorem [10]. The ferromagnetic alignment (due to complete delocalization) competes with the antiferromagnetic spin coupling (due to superexchange processes between neighboring occupied sites). Which process dominates depends on the strength of the onsite repulsion u relative to fixed hopping. The interactions v, w tend to increase the threshold value u_{th} for fixed t_{eff} [23]. The gap between the Nagaoka state and the lowest excited state saturates at $\Delta E_{\text{Nag}} \sim 2t_{\text{eff}}$ (Fig. 2) independent of u due to the kinetic origin of the effect. In order to attain an observable effect one should thus have sufficiently large values of both u and t_{eff} . For

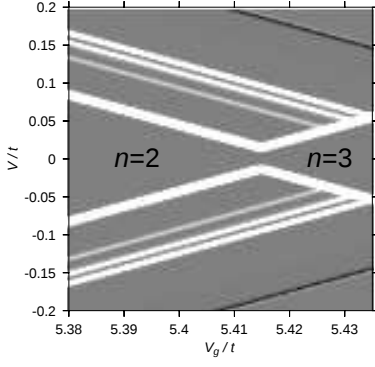


FIG. 3: $dI/dV(V_g, V)$ grayscale plot (white/black ≥ 0) for $u = 5t, v = 2.25t, w = t, \Delta = -10t, T = 2 \cdot 10^{-4}t$.

example, u can be increased by a chemical modification of the ligands which draws charge density into the ligand LUMO orbitals. Taking typical parameters [8] $|\Delta| \approx 1eV, t \approx 10^{-1}eV, \Delta E_{\text{Nag}} \approx 10^{-2}eV$, we estimate $u_{\text{th}} \approx 1eV$ which is reasonable.

Transport— The charge sensitivity of the total spin is observable in the single electron tunneling-current through the molecule. To demonstrate this, we consider the Hamiltonian $H = H_{\text{res}} + H_{\text{eff}} + H_{\text{mol-res}}$, employing units $\hbar = e = k_B = 1$. The electrodes $r = L, R$ are described as electron reservoirs with electrochemical potentials $\mu_r = \mu \pm V/2$ and a constant density of states ρ : $H_{\text{res}} = \sum_{k\sigma r} \epsilon_{k\sigma r} c_{k\sigma r}^\dagger c_{k\sigma r}$. The tunneling term $H_{\text{mol-res}} = (\frac{\Gamma}{2\pi\rho})^{1/2} \sum_{k\sigma jr} t_j^r c_{k\sigma r}^\dagger a_{j\sigma} + h.c.$ describes charge transfer between electrode and molecule (symmetric tunneling barriers). Γ is the overall coupling strength between leads and the molecule and defines the current scale. We assume that tunneling is only possible through two “contact” ligands, namely $t_1^L = t_3^R = 1$, otherwise 0. We have checked that this choice does not cause effects due to orbital symmetry as discussed in [24] by trying also $j = 1, 2$. The coupling to a gate electrode is included in a shift of the single particle energies $\epsilon \rightarrow \epsilon - \alpha V_g$. In the weak tunneling regime ($\Gamma \ll T$) the effect of the leads can be incorporated in the transition rates $\Sigma_{s,s'} = \sum_r \Sigma_{s,s'}^{r,+} + \Sigma_{s,s'}^{r,-}$ between the molecular many-body states s, s' :

$$\begin{aligned} \Sigma_{s,s'}^{r,+} &= \Gamma \sum_{\sigma} f_r^+(E_s - E_{s'}) \left| \sum_j t_j^r \langle s | a_{j\sigma}^\dagger | s' \rangle \right|^2 \\ \Sigma_{s,s'}^{r,-} &= \Gamma \sum_{\sigma} f_r^-(E_s - E_{s'}) \left| \sum_j t_j^r \langle s | a_{j\sigma} | s' \rangle \right|^2. \end{aligned} \quad (5)$$

Here f_r^+ is the Fermi function of reservoir r and $f_r^- = 1 - f_r^+$. Importantly, the matrix elements include the calculated many-body wavefunction of the molecule and the spin selection rules. From the stationary master equation $\sum_{s'} (\Sigma_{s,s'} P_{s'} - \Sigma_{s',s} P_s) = 0$ we obtain the non-equilibrium occupations P_s of the molecular states s and the resulting stationary current which may be calculated

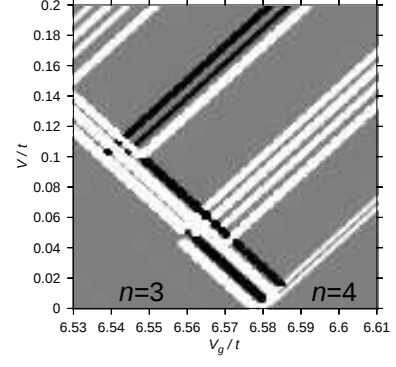


FIG. 4: Same parameters as Fig. 3 except $u = 4.05t$ and around a different charge degeneracy point.

at either electrode $r = L, R$:

$$I_r = - \sum_{s,s'} (\Sigma_{s,s'}^{r,+} P_{s'} - \Sigma_{s',s}^{r,-} P_s). \quad (6)$$

Due to the presence of a maximal spin state, either as ground or excited state, spin blockade and NDC effects occur, respectively [25].

Maximal spin ground state — For $u > u_{\text{th}}$ and fixed t the *ground state* for $n = 3, 5$ is a Nagaoka state (Fig. 2). Transport involving groundstates $n \leftrightarrow n + 1$ for $n = 2, \dots, 5$ is completely blocked for *small bias* and low temperature ($T, V < \Delta E_{\text{Nag}}$): the Coulomb diamonds in a differential conductance versus (V_g, V) plot do not close (Fig. 3). Since the ground state spin is either 0 ($n = 2, 4, 6$) or $3/2$ ($n = 3, 5$) the tunneling rates between neighboring ground states vanish: even when ground state transitions are energetically allowed, due to the spin selection rule $\Delta S = 1/2$ transport is completely blocked in the weak tunneling limit. However, when temperature or voltage are increased, such that the first excited state with appropriate spin can be accessed, current begins to flow.

Maximal-spin excited state — Depending on the gate voltage, NDC and even complete current blocking can occur at *finite bias voltage* [25] when the Nagaoka state is the lowest spin-excitation for $n = 3, 5$ (i.e. $u \lesssim u_{\text{th}}$, Fig. 2). The typical result is depicted in Fig. 4. Near the charge $3 \leftrightarrow 4$ degeneracy point (and $4 \leftrightarrow 5$) two NDC lines (black) with negative slope appear which are due to the low lying $S = 3/2$ Nagaoka state. We first discuss the lower NDC line using the left scheme in Fig. 5. At the charge degeneracy point ($V_g/t \sim 6.58$ in Fig. 4) the current sets on because a transport channel is opened, namely $n = 3, S = 1/2$ (2-fold degenerate) $\leftrightarrow n = 4, S = 0$. Increasing the bias voltage by Δ_4 results in a gain in population of the Nagaoka state via the $n = 4, S = 1$ excited state. Since the Nagaoka state cannot decay (strictly) to the $n = 4, S = 0$ ground state the number of transport channels is therefore decreased from two to one leading to the lower NDC effect. Further away from the degeneracy point ($V_g/t \lesssim 6.56$ in Fig. 4), the lower NDC line turns into a conductance

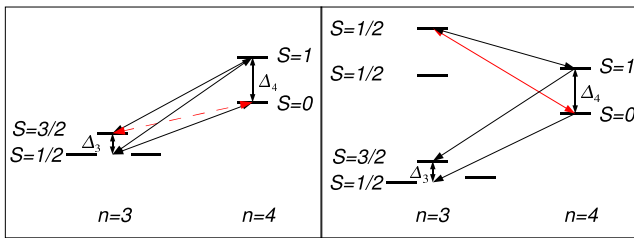


FIG. 5: Minimal set of states for the lower NDC effect (left) and the complete current suppression (right) in Fig. 4.

peak and simultaneously the ground-state transition line below it disappears. This is due to a complete population inversion between the ground and excited state for $n = 3$ which already occurs inside the Coulomb diamond. When the transition from $n = 4, S = 0$ to the third excited state $n = 3, S = 1/2$ lies in the bias window, the Nagaoka state is occupied starting from the ground-state $n = 3, S = 1/2$ via the cascade of single-electron tunneling processes indicated in the right panel of Fig. 5. It is *fully* occupied because the escape rate from $n = 3, S = 3/2$ relative to that from $n = 3, S = 1/2$ ground-state is suppressed by a factor $\sim e^{-(\Delta_4 - \Delta_3)/T} \ll 1$ (Fig. 5). The upper NDC line with negative slope in Fig. 4 is caused by the occupation of the high lying maximal-spin state $n = 4, S = 2$ which cannot decay to states with one electron less and higher spin [25]. This state can already be reached at low

voltages only due the presence of the low-lying Nagaoka state $S = 3/2$ at $n = 3$.

Conclusion— We have shown that in particular types of single-molecule devices the Nagaoka spin-polarization mechanism is relevant since the Coulomb blockade effect allows the controlled addition of single electrons (in contrast to the case of bulk magnets). The magnetic properties of the molecule may thus be switched by a gate voltage. The fingerprints of this charge-selective stabilization of maximal spin states (either a ground or a low-lying excited state) are observable in the tunneling current. We also have investigated an extension of the model considered here with a spin degree of freedom added to each of the four metal ions [26]. In this more complicated case the cooperative spin-polarization effect (of both Nagaoka-origin and direct ion-ligand exchange) compete with the antiferromagnetic superexchange (induced by ion-ligand hopping). It is found that the Nagaoka state is also relevant here and that its transport fingerprints are the same as demonstrated in this work for a generic model.

We thank M. Ruben and J. Kortus for stimulating discussions. M. R. W. acknowledges the financial support provided through the European Community's Research Training Networks Program under contract HPRN-CT-2002-00302, Spintronics.

-
- [1] M. Ruben, J. Rojo, F. Romero-Salguero, L. Uppadine, and J.-M. Lehn, *Angew. Chem. Int. Ed.* (2004).
 - [2] L. Zhao, C. Matthews, L. Thomson, and S. Heath, *Chem. Commun.* **4**, 265 (2000).
 - [3] O. Waldmann, L. Zhao, and L. K. Thompson, *Phys. Rev. Lett.* **88**, 066401 (2002).
 - [4] O. Waldmann, S. Carretta, P. Santini, R. Koch, A. G. M. Jansen, G. Amoretti, R. Caciuffo, L. Zhao, and L. K. Thompson, *Phys. Rev. Lett.* **92**, 096403 (2004).
 - [5] T. Guidi, S. Carretta, P. Santini, E. Liviotti, N. Magnani, C. Mondelli, O. Waldmann, L. K. Thompson, L. Zhao, C. D. Frost, et al., *Phys. Rev. B* **69**, 104432 (2004).
 - [6] O. Waldmann, J. Hassmann, P. Müller, G. S. Hanan, D. Volkmer, U. S. Schubert, and J.-M. Lehn, *Phys. Rev. Lett.* **78**, 3390 (1997).
 - [7] O. Waldmann, M. Ruben, U. Ziener, and J.-M. Lehn, preprint.
 - [8] M. Ruben, E. Breuning, M. Barboui, J.-M. Gisselbrecht, and J.-M. Lehn, *Chem. Eur. J.* **9**, 291 (2003).
 - [9] A. A. Vlček, *Coord. Chem. Rev.* **43**, 39 (1982).
 - [10] Y. Nagaoka, *Phys. Rev.* **147**, 392 (1966).
 - [11] H. Tasaki, *Progress of Theoretical Physics* **99**, 489 (1998).
 - [12] J.-M. Lehn, *Supramolecular chemistry: Concepts and perspectives* (VCH, Weinheim, 1995).
 - [13] H. Park, J. Park, A. K. L. Lim, E. H. Anderson, A. P. Alivisatos, and P. L. McEuen, *Nature* **407**, 57 (2000).
 - [14] J. Park, A. Pasupathy, J. I. Goldsmith, C. Chang, Y. Yaish, J. R. Petta, M. Rinkoski, J. Sethna, H. D. Abruna, P. L. McEuen, et al., *Nature* **417** (2002).
 - [15] W. Liang, M. P. Shores, M. Bockrath, J. R. Long, and H. Park, *Nature* **417**, 725 (2002).
 - [16] R. Arita, Y. Suwa, K. Kuroki, and H. Aoki, *Phys. Rev. Lett.* **88**, 127202 (2002).
 - [17] P. Huai, Y. Shimo, and S. Abe, *Phys. Rev. Lett.* **90**, 207203 (2003).
 - [18] J. B. Torrence, J. E. Vazquez, J. J. Mayerle, and V. Y. Lee, *Phys. Rev. Lett.* **46**, 253 (1981).
 - [19] S. Ishihara, T. Egami, and M. Tachiki, *Phys. Rev. B* **49**, 8944 (1994).
 - [20] T. Kuzmenko, K. Kikoin, and Y. Avishai, *Phys. Rev. B* **69**, 195109 (2004).
 - [21] K. Kikoin and Y. Avishai, *Phys. Rev. B* **65**, 115329 (2002), and references therein.
 - [22] J. Schrieffer and P. Wolff, *Phys. Rev.* **149**, 491 (1966).
 - [23] M. Kollar, R. Strack, and D. Vollhardt, *Phys. Rev. B* **53**, 9225 (1996).
 - [24] M. H. Hettler, W. Wenzel, M. R. Wegewijs, and H. Schoeller, *Phys. Rev. Lett.* **90**, 076805 (2003).
 - [25] D. Weinmann, W. Häusler, and B. Kramer, *Phys. Rev. Lett.* **74**, 984 (1995).
 - [26] C. Romeike, M. R. Wegewijs, W. Wenzel, M. Ruben, and H. Schoeller, preprint.